

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A silicon focus ring comprising silicon single crystal used as a focus ring in a plasma apparatus, wherein, in order to produce an intrinsic heavy metal gettering effect of the focus ring, a concentration of interstitial oxygen contained in the silicon focus ring is not less than 5×10^{17} atoms/cm³ and not more than 1.5×10^{18} atoms/cm³, and a nitrogen concentration in the silicon focus ring is not less than 5×10^{13} number/cm³ and not more than 5×10^{15} number/cm³, the intrinsic gettering effect exceeding a corresponding effect for silicon not doped with interstitial oxygen and nitrogen, and the surface of the silicon focus ring is subjected to etching treatment to remove a mechanical damage layer.

2-4. (Cancelled)

5. (Currently Amended) A producing method for a silicon focus ring of a single crystal silicon used for a plasma apparatus, wherein, in order to produce an intrinsic heavy-metal gettering effect of the focus ring, a concentration of interstitial oxygen contained in the silicon focus ring is not less than 5×10^{17} atoms/cm³ and not more than 1.5×10^{18} atoms/cm³, the single crystal silicon is grown by a Czochralski method with doping nitrogen, a nitrogen concentration in the silicon focus ring is not less than 5×10^{13} number/cm³ and not more than 5×10^{15} number/cm³, the single crystal silicon is processed in a circle, and a silicon ring is produced, and the surface of the silicon focus ring is subjected to etching treatment to remove a mechanical damage layer, the intrinsic gettering effect exceeding a corresponding effect for silicon not doped with interstitial oxygen and nitrogen.

6-7. (Cancelled)